

Two-line TVS Diode

## **General Description**

The AOZ8222DI-05 is a two-line transient voltage suppressor diode designed to protect voltage sensitive electronics from high transient conditions and ESD.

This device incorporates two TVS diodes in an ultra-small DFN 1.0 x 0.6 package. During transient conditions, the TVS diodes directs the transient to ground. The AOZ8222DI-05 may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 ( $\pm$  15 kV air,  $\pm$  8 kV contact discharge).

The AOZ8222DI-05 comes in an RoHS compliant 3-lead DFN package and is rated over a -40 °C to +85 °C ambient temperature range.

The ultra-small 1.0 mm x 0.6 mm x 0.5 mm DFN package makes it ideal for applications where PCB space is a premium. The small size and high ESD protection makes it ideal for protecting voltage sensitive electronics from high transient conditions and ESD.

#### **Features**

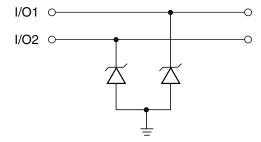
- ESD protection for high-speed data lines:
  - Exceeds IEC 61000-4-2 (ESD): ± 20 kV (air),
    ± 20 kV (contact)
  - Human Body Model (HBM) ± 30 kV
- Small package saves board space
- Low insertion loss
- Low clamping voltage
- Low operating voltage: 5 V

## **Applications**

- Portable handheld devices
- Keypads, data lines, buttons
- Notebook computers
- Digital Cameras
- Portable GPS
- MP3 players

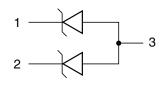


# **Typical Application**



**Unidirection Protection of Two Line** 

# **Pin Configuration**





## **Ordering Information**

Part Number	Ambient Temperature Range	Package	Environmental		
AOZ8222DI-05	-40 °C to +85 °C	DFN 1.0 x 0.6-3L	Green Product		



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant.

 $Please\ visit\ www.aosmd.com/media/AOSGreen Policy.pdf\ for\ additional\ information.$ 

### **Absolute Maximum Ratings**

Exceeding the Absolute Maximum ratings may damage the device.

Parameter	AOZ8222DI-05DI-05				
Peak Pulse Current, t <sub>P</sub> = 8/20 μs	5.5 A				
Peak Pulse Power, t <sub>P</sub> = 8/20 μs	50 W				
Storage Temperature (T <sub>S</sub> )	-65 °C to +150 °C				
ESD Rating per IEC61000-4-2, Contact <sup>(1)</sup>	± 20 kV				
ESD Rating per IEC61000-4-2, Air <sup>(1)</sup>	± 20 kV				
ESD Rating per Human Body Model <sup>(2)</sup>	± 30 kV				

### Notes:

- 1. IEC 61000-4-2 discharge with C\_Discharge = 150 pF, R\_Discharge = 330  $\Omega.$
- 2. Human Body Discharge per MIL-STD-883, Method 3015  $C_{Discharge}$  = 100 pF,  $R_{Discharge}$  = 1.5 k $\Omega$ .

# **Maximum Operating Ratings**

Parameter	Rating
Junction Temperature (T <sub>J</sub> )	-40 °C to +125 °C



## **Electrical Characteristics**

T<sub>A</sub> = 25 °C unless otherwise specified.

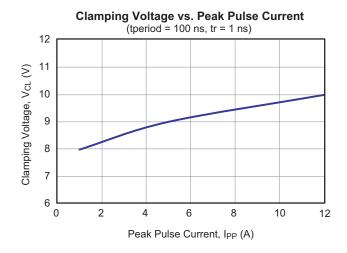
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit s
V <sub>RWM</sub>	Reverse Working Voltage	Between I/O and VN <sup>(3)</sup>			5.0	٧
V <sub>BR</sub>	Reverse Breakdown Voltage	I <sub>T</sub> = 1 mA, between I/O and VN <sup>(4)</sup>	6.0			V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> = 5 V, between I/O and VN			1	μA
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 10 mA	0.6	0.7	0.9	V
V <sub>CL</sub>	Channel Clamp Voltage Positive Transients Negative Transients	$I_{PP}$ = 1 A, tp = 100 ns, any I/O pin to Ground <sup>(5)(6)</sup>			8.0 -2.0	V V
	Channel Clamp Voltage Positive Transients Negative Transients	$I_{PP}$ = 5 A, tp = 100 ns, any I/O pin to Ground <sup>(5)(6)</sup>			9.0 -5.0	V V
	Channel Clamp Voltage Positive Transients Negative Transients	I <sub>PP</sub> = 12 A, tp = 100 ns, any I/O pin to Ground <sup>(5)(6)</sup>			10.0 -10.0	V V
СЈ	Channel Input Capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, between I/O pins <sup>(6)</sup>		8	9	pF
		V <sub>R</sub> = 0 V, f = 1 MHz, any I/O pin to Ground <sup>(6)</sup>		15	18	pF

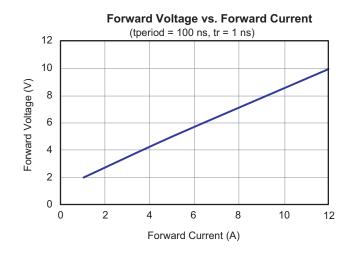
#### Notes:

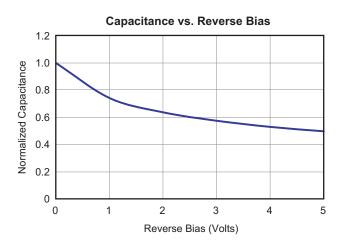
- 3. The working peak reverse voltage, VRWM, should be equal to or greater than the DC or continuous peak operating voltage level.
- 4.  $V_{BR}$  is measured at the pulse test current  $I_T$ .
- 5. Measurements performed using a 100ns Transmission Line Pulse (TLP) system.
- 6. Guaranteed by design and characterization.

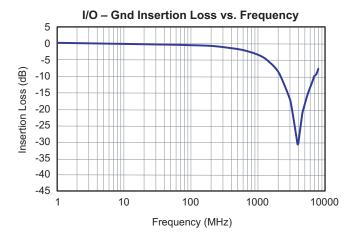


# **Typical Performance Characteristics**



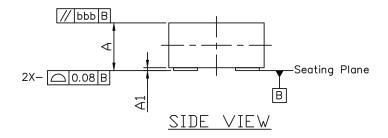


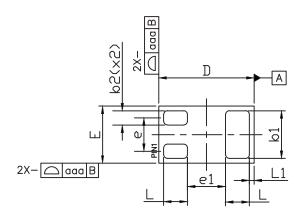






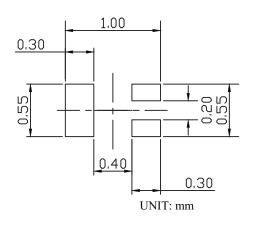
# Package Dimensions, DFN1.0x0.6





BOTTOM VIEW

### RECOMMENDED LAND PATTERN



SYMBOLS	DIMENS	IONS IN MIL	LIMETERS	DIMENSIONS IN INCHES				
STMBULS	MIN	NDM	MAX	MIN	NDM	MAX		
Α	0.47	0.52	0.55	0.019	0.020	0.022		
A1	0.00	0.03	0.05	0.000	0.001	0.002		
b1	0.45 0.50		0.55	0.018	0.020	0.022		
b2	0.10	0.15	0.20	0.004	0.006	0.008		
D	0.95	1.00	1.05	0.037	0.039	0.041		
E	0.55	0.60	0.65	0.022	0.024	0.026		
е		0.35			0.014			
e1	0.40				0.016			
L	0.20	0.25	0.30	0.008	0.010	0.012		
L1	0.05				0.002			
aaa		0.15		0.006				
bbb		0.05		0.002				

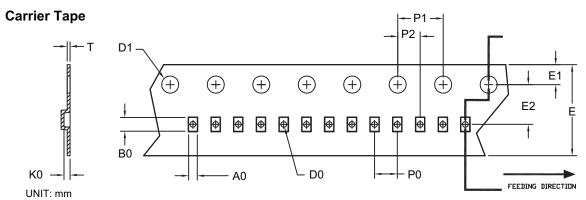
### **NOTE**

- 1. ALL DIMENSION ARE IN MILLIMETERS.ANGLES ARE IN DEGREES.
- 2. COPLANARITY APPLIES TO THE EXPOSED HEAT SINK SLUG AS WELL AS THE TERMINALS.

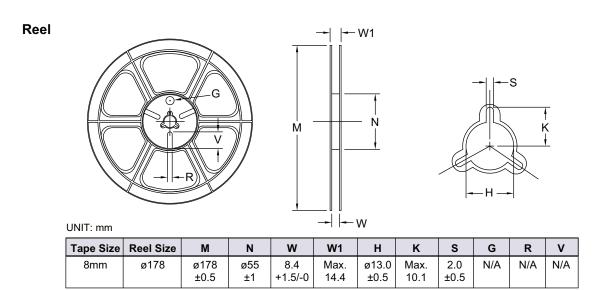
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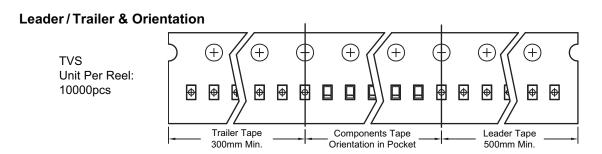


# Tape and Reel Dimensions, DFN1.0x0.6



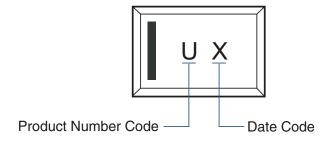
Option	Package	A0	В0	K0	D0	D1	E	E1	E2	P0	P1	P2	Т
А	DFN 1.0x0.6/ DFN 1.0x0.6A (8 mm)	0.69 ±0.05	1.19 ±0.05	0.66 ±0.05	0.40 ±0.05	1.50 ±0.10	8.00 +0.3/-0.1	1.75 ±0.10	3.50 ±0.05	2.00 ±0.05	4.00 ±0.10	2.00 ±0.05	0.23 ±0.02
В	DFN 1.0x0.6/ DFN 1.0x0.6A (8 mm)	0.65 ±0.04	1.05 ±0.04	0.61 ±0.04	0.40 ±0.05	1.50 ±0.10	8.00 +0.3/-0.1	1.75 ±0.10	3.50 ±0.05	2.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.20 ±0.05







## Part Marking



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